- Designed for Complementary Use with TIP120, TIP121 and TIP122
- 65 W at 25°C Case Temperature
- 5 A Continuous Collector Current
- Minimum h_{FE} of 1000 at 3 V, 3 A

Pin 2 is in electrical contact with the mounting base.

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absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	MA	SYMBOL	VALUE	UNIT
THE COMPANY OF COMPANY	TIP125	TOON CO	-60	
Collector-base voltage (I _E = 0)	TIP126	V_{CBO}	-80	V
	TIP127	W.1001.	-100	
M. COM THE WAY CO. T.	TIP125	100X.C	-60	
Collector-emitter voltage (I _B = 0)	TIP126	V _{CEO}	-80	V
	TIP127	11 100 1.	-100	
Emitter-base voltage	TV W	V _{EBO}	-5	V
Continuous collector current		Ic	CO -5	Α
Peak collector current (see Note 1)	(1,1,1)	I _{CM}	-8	Α
Continuous base current	TT	I _B	-0.1	Α
Continuous device dissipation at (or below) 25°C case temperature (see Not	te 2)	P _{tot}	65	W
Continuous device dissipation at (or below) 25°C free air temperature (see N	Note 3)	P _{tot}	2	W
Unclamped inductive load energy (see Note 4)	WILL	½LI _C ²	50	mJ
Operating junction temperature range	OW	Ti	-65 to +150	°C
Storage temperature range	COMIT	T _{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds	· CTIV	TL	260	°C

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%.$

- 2. Derate linearly to 150°C case temperature at the rate of 0.52 W/°C.
- 3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.
- 4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = -5 mA, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = -20 V.

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TIP125, TIP126, TIP127 PNP SILICON POWER DARLINGTONS

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electrical characteristics at 25°C case temperature

	PARAMETER	COM	TEST CONDITIO	ONS	MIN	TYP	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = -30 mA (see Note 5)	I _B = 0	TIP125 TIP126 TIP127	-60 -80 -100			V
I _{CEO}	Collector-emitter cut-off current	$V_{CE} = -30 \text{ V}$ $V_{CE} = -40 \text{ V}$ $V_{CE} = -50 \text{ V}$	$I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$	TIP125 TIP126 TIP127	WT		-0.5 -0.5 -0.5	mA
I _{CBO}	Collector cut-off current	$V_{CB} = -60 \text{ V}$ $V_{CB} = -80 \text{ V}$ $V_{CB} = -100 \text{ V}$	I _E = 0 I _E = 0 I _E = 0	TIP125 TIP126 TIP127	M.T	N	-0.2 -0.2 -0.2	mA
I _{EBO}	Emitter cut-off current	V _{EB} = -5 V	I _C = 0	WWW.100Y.C	OM	TW	-2	mA
h _{FE}	Forward current transfer ratio	$V_{CE} = -3 V$ $V_{CE} = -3 V$	$I_{C} = -0.5 \text{ A}$ $I_{C} = -3 \text{ A}$	(see Notes 5 and 6)	1000 1000	LTW	Ĩ	
V _{CE(sat)}	Collector-emitter saturation voltage	$I_B = -12 \text{ mA}$ $I_B = -20 \text{ mA}$	$I_C = -3 A$ $I_C = -5 A$	(see Notes 5 and 6)	N.CO	M.I	-2 N -4	V
V_{BE}	Base-emitter voltage	V _{CE} = -3 V	I _C = -3 A	(see Notes 5 and 6)	OY.C	OW.	-2.5	V
V _{EC}	Parallel diode forward voltage	I _E = -5 A	I _B = 0	(see Notes 5 and 6)	001.	COM	-3.5	V

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu s$, duty cycle $\leq 2\%$.

thermal characteristics

erma	I characteristics				
MA	PARAMETER	MIN	TYP	MAX	UNI
$R_{\theta JC}$	Junction to case thermal resistance	N TAN	100 x.	1.92	°C/V
$R_{\theta JA}$	Junction to free air thermal resistance	O WW	. 001	62.5	°C/V

resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	COM^{-1}	TEST CONDITION	s ton	MIN	TYP	MAX	UNIT
t _{on}	Turn-on time	I _C = -3 A	I _{B(on)} = -12 mA	I _{B(off)} = 12 mA		1.5	00	μs
t _{off}	Turn-off time	V _{BE(off)} = 5 V	$R_1 = 10 \Omega$	$t_{\rm p} = 20 \ \mu \rm s, \ dc \le 2\%$	< %	8.5	~~~	μs

 $^{^{\}dagger}$ Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.al; WWW.100Y.COM

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^{6.} These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts. WWW.I

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TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN VS **COLLECTOR CURRENT** TCS125AA $T_c = -40^{\circ}C$ T_c = 25°C $T_c = 100$ °C 10000 Current 20 **Typical** 1000 h. $V_{CE} = -3 V$ = 300 µs, duty cycle < 2% 100 -0-5 -1-0 I_c - Collector Current - A

COLLECTOR-EMITTER SATURATION VOLTAGE

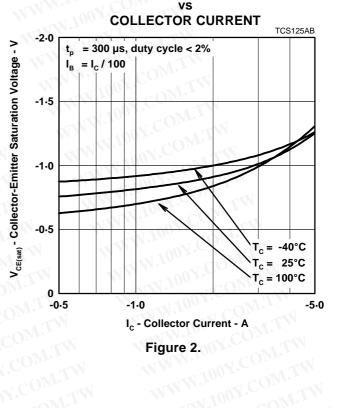
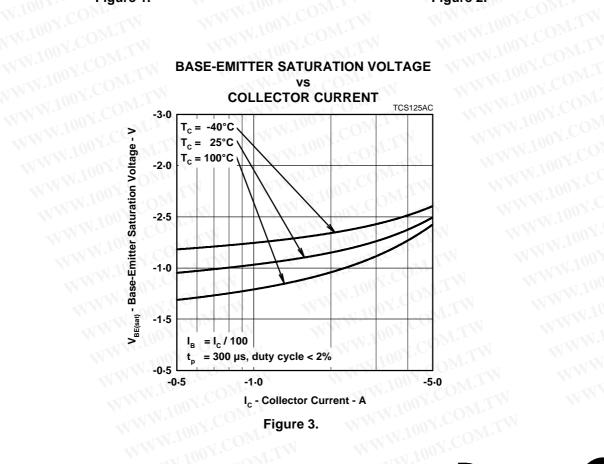


Figure 1.

BASE-EMITTER SATURATION VOLTAGE



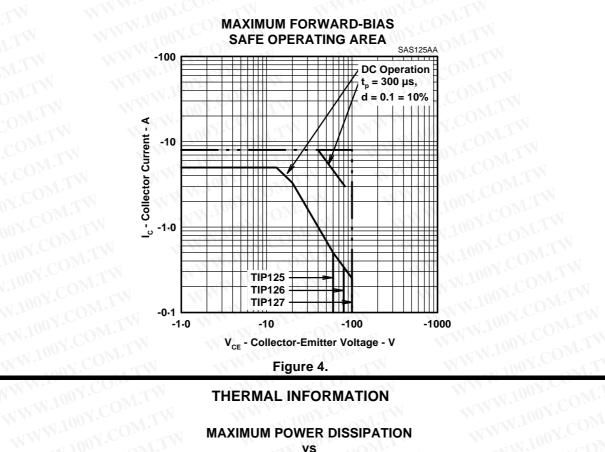


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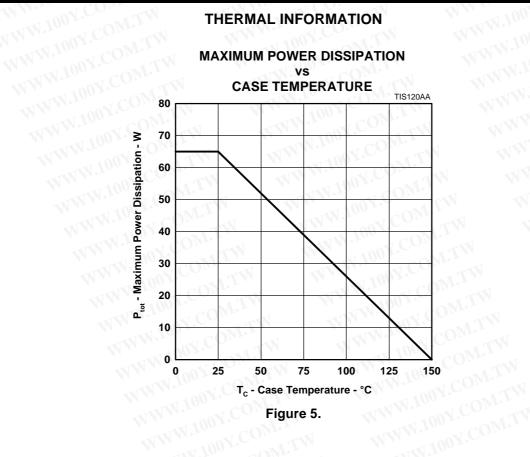
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MAXIMUM SAFE OPERATING REGIONS



THERMAL INFORMATION

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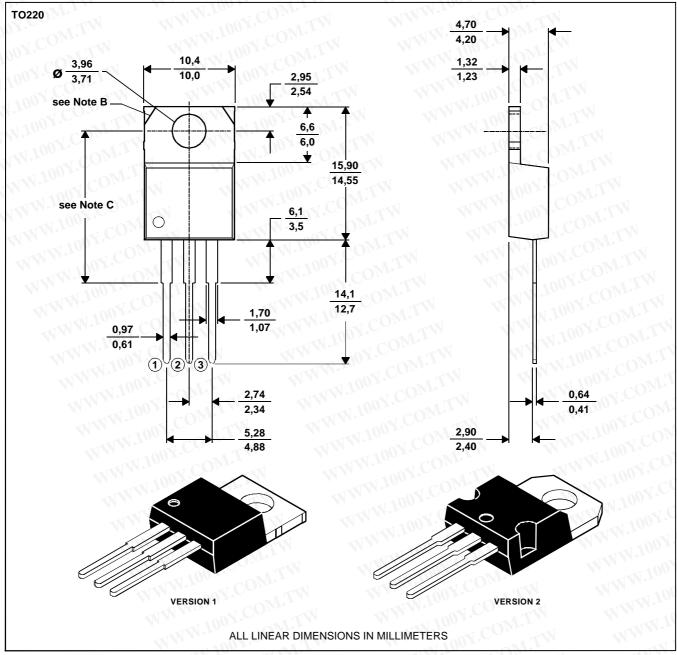
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MECHANICAL DATA

TO-220

3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTES: A. The centre pin is in electrical contact with the mounting tab.

- B. Mounting tab corner profile according to package version.
- C. Typical fixing hole centre stand off height according to package version. Version 1, 18.0 mm. Version 2, 17.6 mm.

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